

Features

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- High density cell design for low $R_{DS(ON)}$
- Fast Switching Speed
- Green Device Available

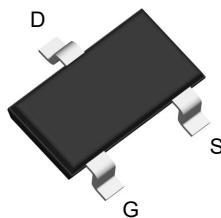
Product Summary



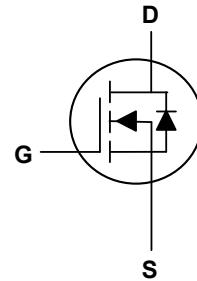
V_{DS}	100	V
I_D	0.17	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	6	Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	10	Ω

Applications

- Small servo motor control
- Power MOSFET gate drivers
- Switching application



SOT23 Top View



Absolute Maximum Ratings($T_A=25^\circ C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	I_D	0.17	A
Pulsed Drain Current ²	I_{DM}	0.68	A
Total Power Dissipation ³	P_D	250	mW
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	---	620	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	100	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$, $I_D=0.17\text{A}$	---	3.5	6	Ω
		$V_{\text{GS}}=4.5\text{V}$, $I_D=0.17\text{A}$	---	4.5	10	Ω
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$, $I_D=250\mu\text{A}$	1	1.8	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=100\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
Total Gate Charge	Q_g	$V_{\text{DS}}=50\text{V}$, $V_{\text{GS}}=10\text{V}$, $I_D=0.2\text{A}$	---	2.3	---	nC
Turn-On Delay Time	$T_{\text{d}(\text{on})}$	$V_{\text{DD}}=50\text{V}$, $V_{\text{GS}}=10\text{V}$, $R_G=6\Omega$, $I_D=0.2\text{A}$	---	8.8	---	ns
Rise Time	T_r		---	9.2	---	
Turn-Off Delay Time	$T_{\text{d}(\text{off})}$		---	18.5	---	
Fall Time	T_f		---	7.9	---	
Input Capacitance	C_{iss}	$V_{\text{DS}}=50\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	34	---	pF
Output Capacitance	C_{oss}		---	11	---	
Reverse Transfer Capacitance	C_{rss}		---	7	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ¹	I_s		---	---	0.17	A
Diode Forward Voltage ²	V_{SD}	$V_{\text{GS}}=0\text{V}$, $I_s=0.2\text{A}$, $T_J=25^\circ\text{C}$	---	---	1.2	V

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature

Typical Characteristics

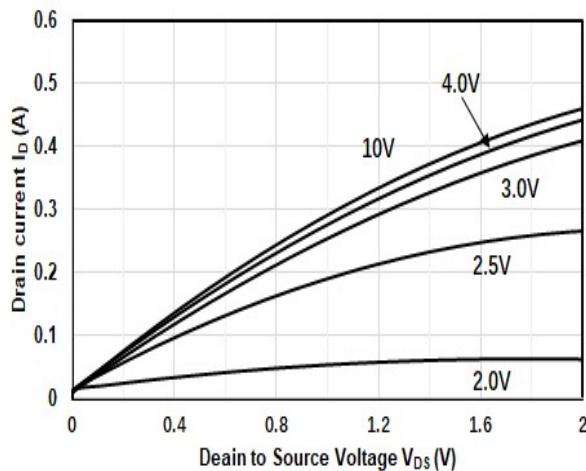


Figure1. Output Characteristics

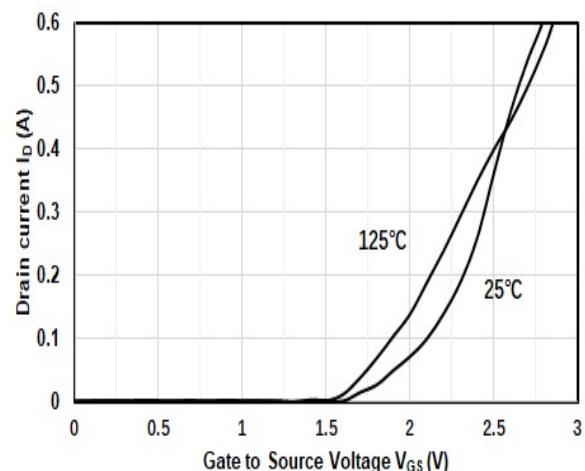


Figure2. Transfer Characteristics

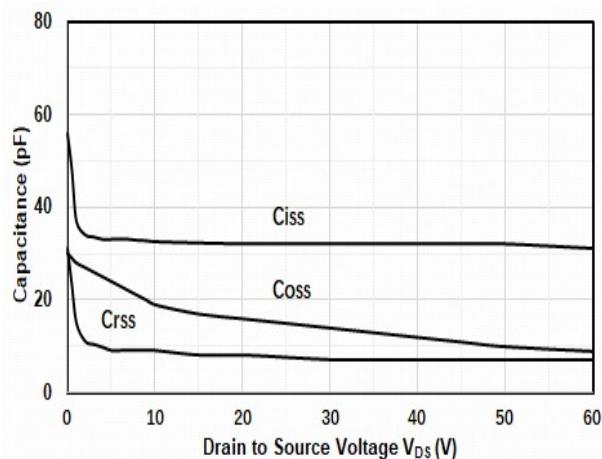


Figure3. Capacitance Characteristics

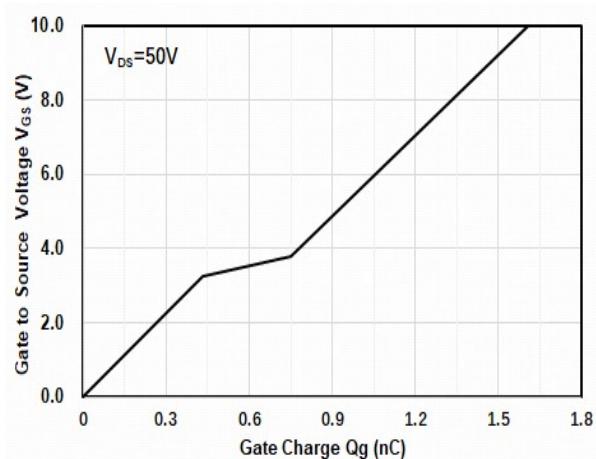


Figure4. Gate Charge

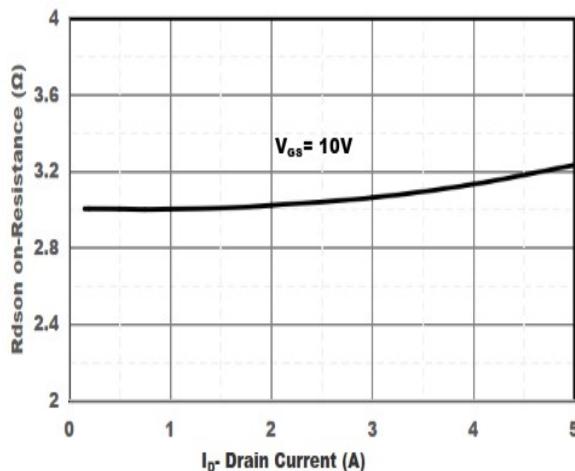


Figure5. Drain-Source on Resistance

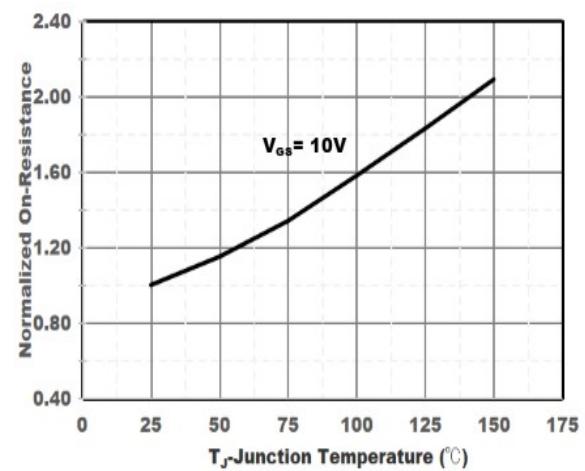


Figure6. Drain-Source on Resistance

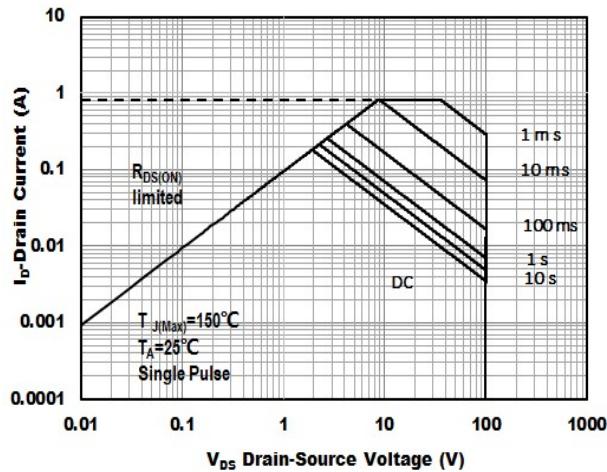


Figure7. Safe Operation Area

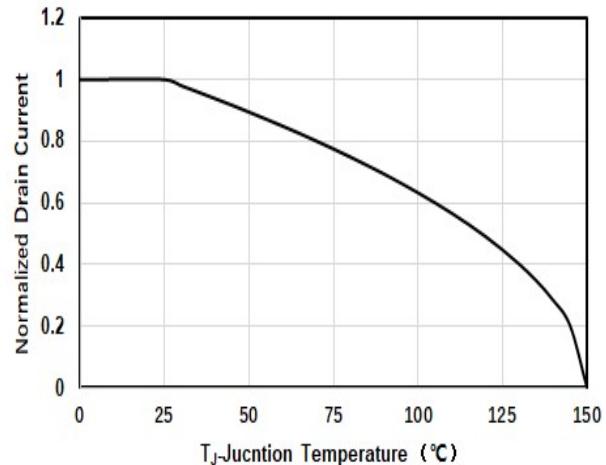
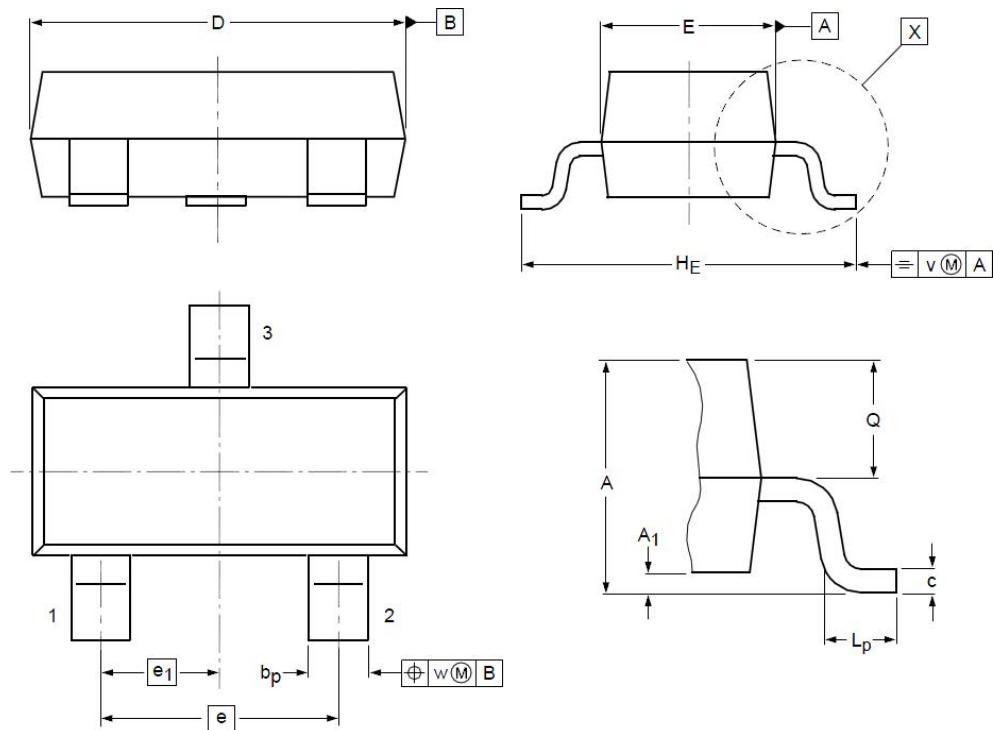


Figure8. Drain-Source Current

SOT23 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.90	1.05	1.20	e₁	--	0.95	--
A₁	0.01	0.05	0.10	H_E	2.10	2.40	2.50
b_p	0.38	0.42	0.48	L_P	0.40	0.50	0.60
c	0.09	0.13	0.15	Q	0.45	0.49	0.55
D	2.80	2.92	3.00	V	--	0.20	--
E	1.20	1.33	1.40	W	--	0.10	--
e	--	1.90	--				